

N-CHANNEL MOSFET

Qualified per MIL-PRF-19500/592

DEVICES

2N7225 2N7225U

LEVELS

JAN
JANTX
JANTXV

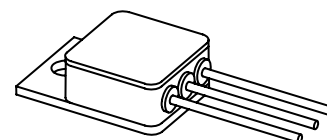
ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	200	Vdc
Gate – Source Voltage	V_{GS}	± 20	Vdc
Continuous Drain Current $T_C = +25^\circ\text{C}$	I_{D1}	27.4	Adc
Continuous Drain Current $T_C = +100^\circ\text{C}$	I_{D2}	17	Adc
Max. Power Dissipation $T_C = +25^\circ\text{C}$	P_{tl}	150 ⁽¹⁾	W
Drain to Source On State Resistance	$R_{ds(on)}$	0.1 ⁽²⁾	Ω
Operating & Storage Temperature	T_{op}, T_{stg}	-55 to +150	$^\circ\text{C}$

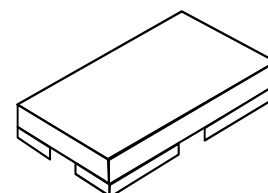
Note: (1) Derated Linearly by 1.2 W/ $^\circ\text{C}$ for $T_C > +25^\circ\text{C}$
(2) $V_{GS} = 10\text{Vdc}$, $I_D = 17\text{A}$

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Drain-Source Breakdown Voltage $V_{GS} = 0\text{V}$, $I_D = 1\text{mAdc}$	$V_{(BR)DSS}$	200		Vdc
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$ $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$, $T_j = +125^\circ\text{C}$ $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$, $T_j = -55^\circ\text{C}$	$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	Vdc
Gate Current $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$ $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$, $T_j = +125^\circ\text{C}$	I_{GSS1} I_{GSS2}		± 100 ± 200	nAdc
Drain Current $V_{GS} = 0\text{V}$, $V_{DS} = 160\text{V}$ $V_{GS} = 0\text{V}$, $V_{DS} = 160\text{V}$, $T_j = +125^\circ\text{C}$	I_{DSS1} I_{DSS2}		25 0.25	μAdc mAdc
Static Drain-Source On-State Resistance $V_{GS} = 10\text{V}$, $I_D = 17\text{A}$ pulsed $V_{GS} = 10\text{V}$, $I_D = 27.4\text{A}$ pulsed $T_j = +125^\circ\text{C}$ $V_{GS} = 10\text{V}$, $I_D = 17\text{A}$ pulsed	$r_{DS(on)1}$ $r_{DS(on)2}$ $r_{DS(on)3}$		0.100 0.105 0.17	Ω Ω Ω
Diode Forward Voltage $V_{GS} = 0\text{V}$, $I_D = 27.4\text{A}$ pulsed	V_{SD}		1.9	Vdc



TO-254AA



U-PKG (U3)
TO-276AB

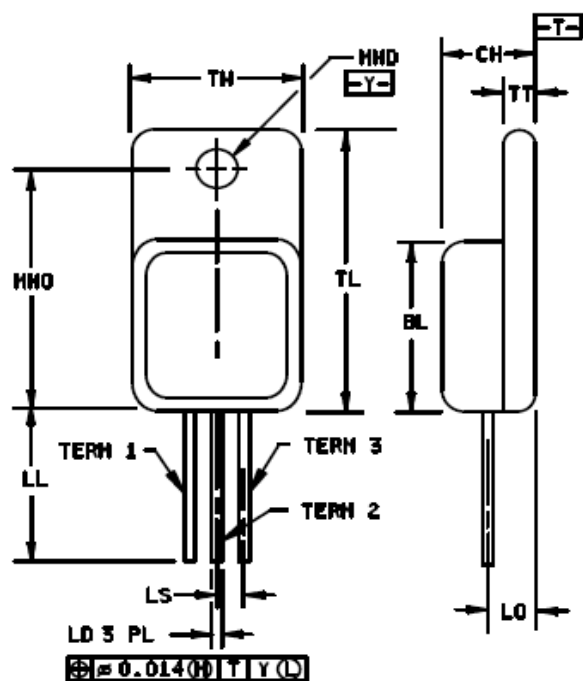
DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate Charge:				
On-State Gate Charge	$Q_{g(on)}$		115	nC
Gate to Source Charge	Q_{gs}		22	
Gate to Drain Charge	Q_{gd}		60	

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Switching time tests:				
Turn-on delay time	$t_{d(on)}$		35	ns
Rinse time	t_r		190	
Turn-off delay time	$t_{d(off)}$		170	
Fall time	t_f		130	
Diode Reverse Recovery Time	t_{rr}		950	ns

PACKAGE DIMENSIONS



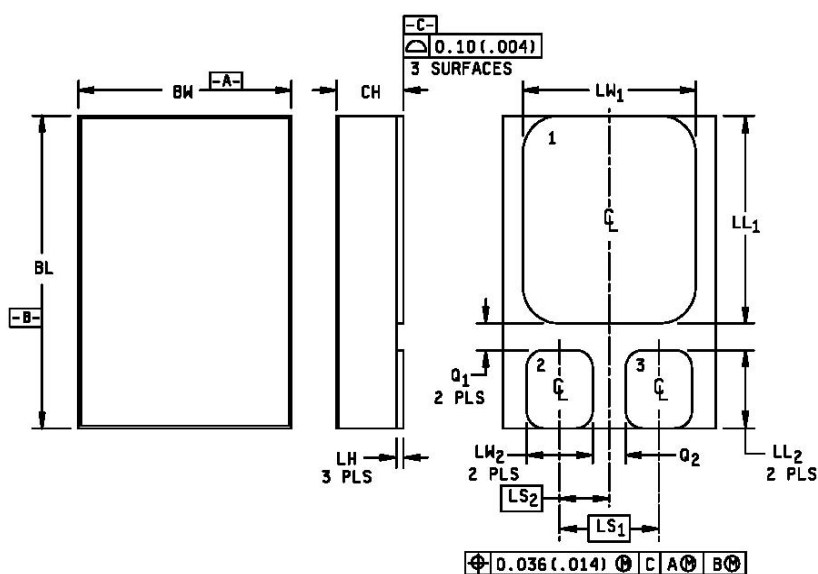
Ltr.	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BL	.535	.545	13.59	13.84	
CH	.249	.260	6.32	6.60	
LD	.035	.045	0.89	1.14	
LL	.510	.570	12.95	14.48	
LO	.150 BSC		3.81 BSC		
LS	.150 BSC		3.81 BSC		
MHD	.139	.149	3.53	3.78	
MHO	.665	.685	16.89	17.40	
TL	.790	.800	20.07	20.32	3, 4
TT	.040	.050	1.02	1.27	
TW	.535	.545	13.59	13.84	3, 4
Term 1	Drain				
Term 2	Source				
Term 3	Gate				

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Glass meniscus included in dimension D and E.
4. All terminals are isolated from the case.
5. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

FIGURE 1. Physical dimensions for TO-254AA

PACKAGE DIMENSIONS



Ltr.	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.620	.630	15.75	16.00
BW	.445	.455	11.30	11.56
CH		.142		3.60
LH	.010	.020	0.26	0.50
LL ₁	.410	.420	10.41	10.67
LL ₂	.152	.162	3.86	4.11
LS ₁	.210 BSC		5.33 BSC	
LS ₂	.105 BSC		2.67 BSC	
LW ₁	.370	.380	9.40	9.65
LW ₂	.135	.145	3.43	3.68
Q ₁	.030		0.76	
Q ₂	.035		0.89	
Term 1	Drain			
Term 2	Source			
Term 3	Gate			

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. The lid shall be electrically isolated from the drain, gate and source.
4. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 2. Dimensions and configuration of surface mount package outline (TO-276AB) 2N7224U, 2N7225U, 2N7227U, and 2N7228U.